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(12)(KR)  
(A)(51) 。 Int. Cl. <sup>7</sup>  
G02F 1/1335(11)  
(43)2002 - 0021332  
2002 03 20(21) 10 - 2001 - 0056360  
(22) 2001 09 13(30) JP - P - 2000 - 00281023 2000 09 14 (JP)  
JP - P - 2000 - 00361069 2000 11 28 (JP)(71) 가 가  
가 가 6 7 35

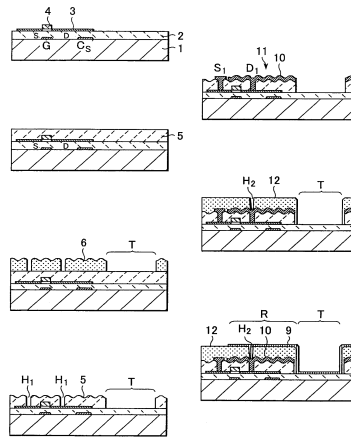
(72) 가 가 6 - 7 - 35 가 가

(74)

:

(54)

, TFT  
 A , B ,  
 C ,  
 D , , , C D .



1 1 1 1

1a 1g .

2a 2b .

3 .

4 .

5 가 .

6 , , .

7 가 .

8 .

9a .

9b 9a .

10a .

10b 10a .

11 .

12a 12g

.

\*

\*

1 : 2 :

3 : 4 :

5 : 6 :

7 : 1 8 : 2

9 : 10 :

11 : 12 :

20 : D :

D<sub>1</sub> : G :

S : S<sub>1</sub> :

T :

,

.

가

,

TFT( )

12a

12i

가

12a

12i

TFT(bottom gate type TFT)

,

TFT

가

.

12a

,

(1)

,

(G)

(Cs)

,

(2)

,

(3)

.

,

(4)가

,

(G)

,

,

(3)

(TFT)가

12b

(5)

(6)

(5)

12c

(T)가

(5)

(H<sub>1</sub>)

(6)

(T)가

(12d).

(H<sub>1</sub>)

TFT

(S)

(S<sub>1</sub>)(H<sub>1</sub>)

TFT

(D)

(D<sub>1</sub>)

12e

가

1 (7)

12f

(D<sub>1</sub>)(S<sub>1</sub>)

2

(H<sub>2</sub>)

(T)

가

2 (8)

1 (7)

(D<sub>1</sub>)

(T)

3

12g

(H<sub>3</sub>)

1 (7)

2 (8)

(T)

(9)

(9)

12h

(D<sub>1</sub>)(H<sub>3</sub>)

(9)

( , )

가

(R)

12i

(10)

, TFT

가

, TFT

12a

12i

TFT(

)

(10)

( )

1 (7)

2 (8)

, TFT

(S)

(D)

(10)

(5)

, 가

(S<sub>1</sub>),(D<sub>1</sub>)

(10)

가 .

가 TFT , 가 , A , 가 , TF  
T B , C , C D .

D , E , F ,  
G , 가 , 가 , F ,

D , E ,  $G_y$  , 가 .  
D ,  $E_x$  , 가 .  
 $G_x$  ,

가 ,  $1/2 \lambda$  ,  $1/4 \lambda$  ,

가 . ,

1a 1g TFT 가

가 , 1a , , (wolfram) 가

(1) , (Cs) (G)

가 , (CVD) (2) (3) (3) ,

가 , (2) 가 ,

가 1% 가 .

가 (4)가 (3) (4) (4)

(G) , (G)가 가 ,

가 , (S) (D)

가 , TFT가 . TFT 가 ,

가 A D .

A , (CVD) (5) ( 1b).

B , (5) (6) .

C , (6) (6) ( 1c). , (S)

(D) , (T) (H<sub>1</sub>) (6)

(6) , (stepper) (6)

가 , 5 ( L/S 6 ) L/S( )

6  
 $L(\mu\text{m})/S(\mu\text{m})$  S( ) 가  
 $L=0.25\mu\text{m}$ ,  $S=0.50\mu\text{m}$ ,  $0.6\mu\text{m}$   
 1200msec 가

6 5 L/S

(index constant)

8 (20) (21)  
 (22)  
 9a (22a)  
 9b 가  
 (6)

(5)

10a (6)  
 10b (6)  
 가

11 (6)  
 (6)

(5) (6) D가 (6)  
 (5)

D C , RIE ICP  
 (H<sub>1</sub>)

D 가 (5)

TFT

TFT

TFT (S) (D) 가 ,  
가 , , ,  
. , ,  
.  
D 1e 1g  
(E G) .  
11) E , , , (H<sub>1</sub>) (S) (S<sub>1</sub>) , (10) ,  
(H<sub>1</sub>) (D) (D<sub>1</sub>) 1E , , ,  
(11) , , ,  
. , , , , .  
(12) F , (12) 1f  
(T) (D<sub>1</sub>)  
(12) 가 , F , , ,  
.  
(12) 1/2 λ 가 , 1/4 λ 가  
. , , (12) .  
G , (9) , 1g  
TFT . (9) , ITO , ,  
(9)  
, (10) , , (9) (9) (H<sub>2</sub>)  
, , (10)  
.  
TFT , 가 ,  
가 , , .  
, F (12) , C  
(6) (T)가 , (12) , (D<sub>1</sub>) (H<sub>2</sub>)  
(10) , (10) (1)  
2) , (10) , (12)  
12) .  
, TFT , (9) G  
TFT , (12) (9)

(10) , (10) , (10)  
 (10) (R) .  
 (12) TFT , (S<sub>1</sub>) , (D<sub>1</sub>) (10) , 3 ,  
 (9) G ,  
 (5) D (S) (S<sub>1</sub>) , E<sub>x</sub> , (9) , (H<sub>1</sub>) (D) (H<sub>1</sub>)  
 (D<sub>1</sub>) , (R) (T) G<sub>x</sub> ,  
 (9) TFT , 4 , (10) , (9) (10) (10) IT  
 O , (11) , (9) ITO ,

이러한 결과를 종합하면, TFT가 사회적 상호작용을 촉진하고, 이는 사회적 상호작용을 통해 사회적 자본을 형성하는 데 기여하는 것으로 보인다. 또한, TFT가 사회적 상호작용을 촉진하는 데 기여하는 것으로 보인다.

A) TFT

B)

C)

가

D) C

2.

1 C D 가

3.

1 가 C

4.

1 D

E)

F)

G)

5.

4 F

가

6.

$\lambda$ ,  $\frac{1}{4}\lambda$  가  $\frac{1}{2}$

7.

1 , D

E) , , ,

$G_y$ ) , .

8.

1 , D

$E_x$ ) , , , ,

$G_x$ ) , .

9.

, , .

10.

9 , , .

11.

10 , ,

$1/2 \lambda$  ,  $1/4 \lambda$  .

12.

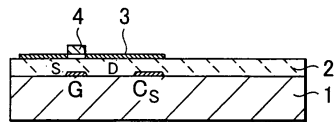
11 , .

13.

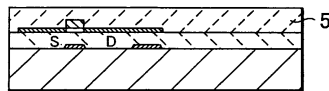
9 , , ,

.

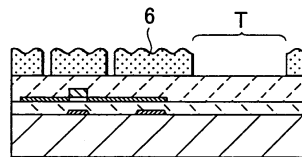
1a



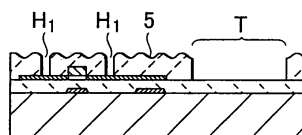
1b



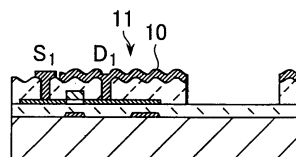
1c



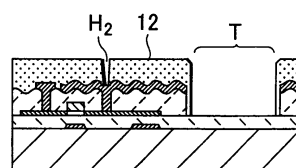
1d



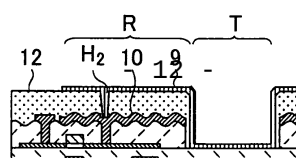
1e



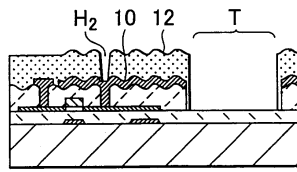
1f



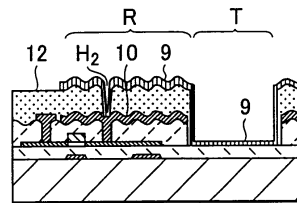
1g



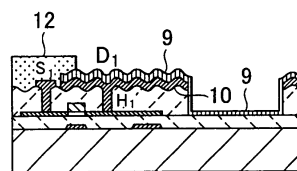
2a



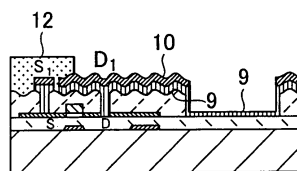
2b



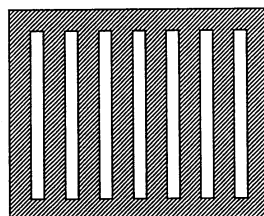
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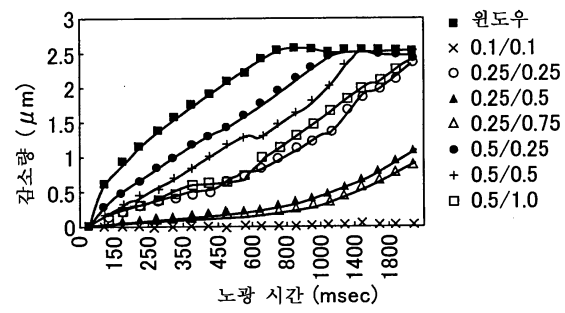
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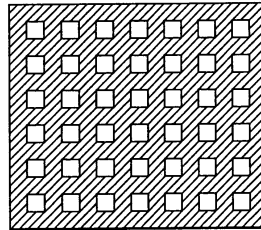
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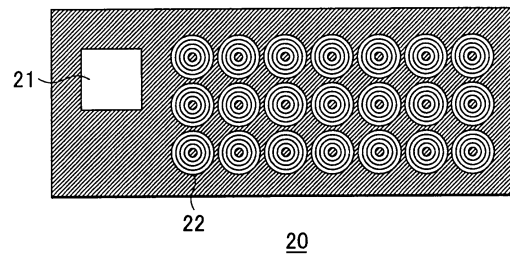
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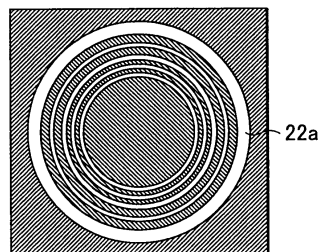
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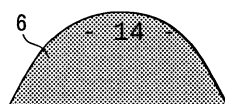
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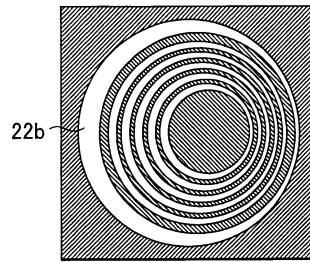
9a



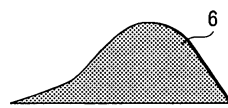
9b



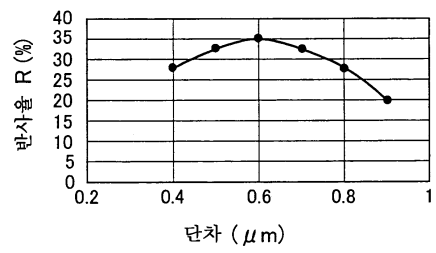
10a



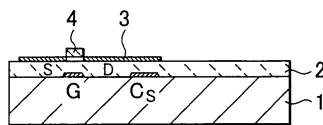
10b



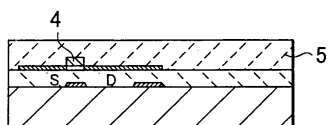
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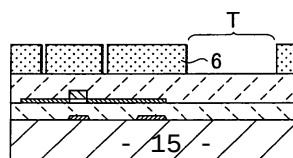
12a



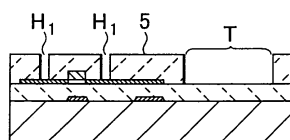
12b



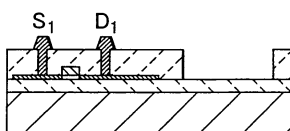
12c



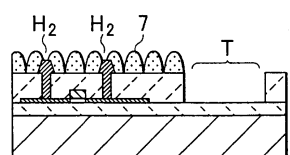
12d



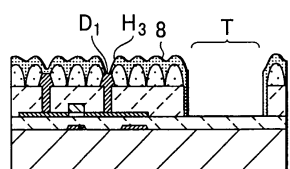
12e



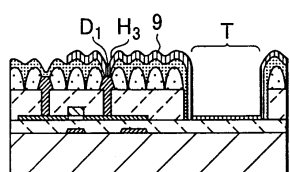
12f



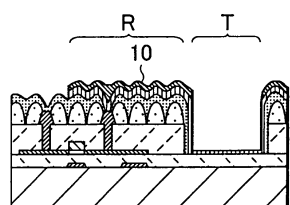
12g



12h



12i



|                |                                                                           |         |            |
|----------------|---------------------------------------------------------------------------|---------|------------|
| 专利名称(译)        | 半透射型液晶显示装置及其制造方法                                                          |         |            |
| 公开(公告)号        | <a href="#">KR1020020021332A</a>                                          | 公开(公告)日 | 2002-03-20 |
| 申请号            | KR1020010056360                                                           | 申请日     | 2001-09-13 |
| [标]申请(专利权)人(译) | 索尼公司                                                                      |         |            |
| 申请(专利权)人(译)    | 索尼公司                                                                      |         |            |
| 当前申请(专利权)人(译)  | 索尼公司                                                                      |         |            |
| [标]发明人         | FUJINO MASAHIRO                                                           |         |            |
| 发明人            | FUJINO,MASAHIRO                                                           |         |            |
| IPC分类号         | G02F1/1368 G02F1/1362 G02F1/1335 H01L29/786 G03F7/20 G02F1/136 H01L21/027 |         |            |
| CPC分类号         | G02F1/133555 G02F1/136227                                                 |         |            |
| 代理人(译)         | 李，何炳<br>李昌勋                                                               |         |            |
| 优先权            | 2000281023 2000-09-14 JP<br>2000361069 2000-11-28 JP                      |         |            |
| 其他公开文献         | KR100845414B1                                                             |         |            |
| 外部链接           | <a href="#">Espacenet</a>                                                 |         |            |

# 摘要(译)

本发明涉及一种制造透反射型液晶显示装置的一个缩短的方法，生产率得到提高有源矩阵型。形成有源矩阵型透射型，在液晶显示器的制造方法，层间绝缘膜形成，形成层间绝缘膜对硅层，以形成源极和TFT的漏极和层间绝缘层的步骤和所述光致抗蚀剂层和B工序，由反射电极的图案是使用掩模形成以下部分分辨率极限形成由和C制造的，以形成一个图案，光致抗蚀剂层中，C相作为蚀刻掩模来蚀刻层间绝缘膜以及用于图案化光致抗蚀剂层的步骤D.在步骤D之后，源电极，信号线，漏电极和反射电极由金属膜同时形成。

- 1 - 指数方面 金属膜，反射电极，透明电极，蚀刻掩模，光致抗蚀剂层

